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QC841 Hybrid Integrated IGBT Driver

QC841 is a hybrid integrated IGBT driver built-in electrical isolation between power devices and control circuits with the high CMRR opto-coupler. Short circuit protection is provided by a built-in desaturation detector. A fault signal is provided if the short circuit protection is activate



FEATURES

- Built in high CMRR opto-coupler (CMR:Typical:30kV/µs, Min.:15kV/µs)
- Electrical isolation voltage between input and output with opto-couplers (Viso=3750VRMS/min)
- Switching frequency up to 20kHz
- Single supply drive topology
- Built in short circuit protection circuit with a pin for fault output
- Soft IGBT turn-off and protection circuit time reset
- Pins are compatible with EXB841

Item		Test Conditions	Limit	Units
Supply Voltage*	Vcc	DC	25	V
Input Voltage	Vı	Between Pin14 and Pin15	-1~+7	V
Photo coupler input current	lin	Between Pin14 and Pin15	25	mA
Output current	I _{g on}	Pulse width 2µs	+5	Α
	I _{g off}	Frequency f=20kHz	-5	Α
Isolation Voltage	Viso	Sinewave voltage 50Hz/60Hz 1 min.	3750	V
Operation Temperature	Topr		-20~+70	°C
Storage Temperature	Tstg	- M - M -	-40~+125	°C
Fault Output Current	I _{FO}		20	mA
Input Voltage	V_{R1}	Pin6 input voltage	50	V

APPLICATION

- I General-purpose Inverter
- AC Servo Systems
- Uninterruptable Power Supplies(UPS)
- Welding Machines

RECOMMENDED MODULES

- 600V Series IGBT(up to 600A)
- 1200V Series IGBT(up to 400A)
- 1700V Series IGBT(up to 200A)

MORNSUN Science & Technology co.,Ltd.

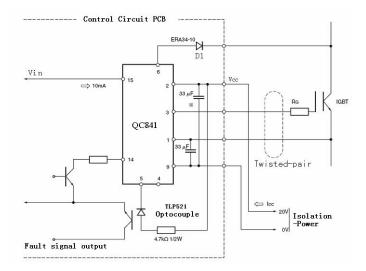
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Http://www.mornsun-power.com

Oh avaat aviatiaa		Test Conditions	Value			1.12
Characteristics	Test Conditions		Min	Тур.	Max	Units
Supply Voltage	Vcc	Recommended Range	18	20	22	V
Pull-up voltage on input side	V _{IN}	Recommended Range	4.75	5	5.25	V
Reverse bias power supply voltage	V_{RB}	Recommended Range		-5		V
"H" input current	I _{IH}	Recommended Range	15.2	16	19	mA
Switching frequency	f	Recommended Range			20	kHz
Gate resistor	R _G	Recommended Range	2			Ω
"H" input current	I _{IH}	V _{IN} =5V	-	16	-	mA
"H" output voltage	V _{OH}	V _{CC} =20V	13	14	-	V
"L" output voltage	V_{OL}	V _{CC} =20V	-	-5	-	V
"L-H" propagation	t _{PLH}	I _{IH} =16mA	-	0.5	1	μs
"L-H" rise time	tr	I _{IH} =16mA		0.6	1	μs
"H-L" propagation	t _{PHL}	I _{IH} =16mA		1	1.3	μs
"H-L" fall time	t _f	I _{IH} =16mA		0.4	1	μs
Protection threshold voltage	V_{OCP}	V _{CC} =20V		8.5		V
Protection reset time	t _{timer}		1	1.4	2	ms
Fault output current	I _{FO}	Pin5 input current, R=4.7K			5	mA
Soft turn-off time	T _{off2}	Pin6: ≥15V, Pin11:open		5		μs
Controlled time detect short circuit 1	T _{trip1}	Pin6: ≥15V, Pin11:open		2.6		μs

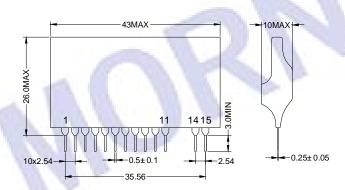
2. "H" represents high level; "L" represents low level.

APPLICATION EXAMPLES



D₁ :Fast Recovery Diode(trr≤0.2µs)

OUTLINE DIMENSIONS (UNIT:MM)



PIN FUNCTION:

Pin number	Description				
1	Connected to smoothing capacitor for reverse bias				
2	Power supply(+)				
3	Drive output				
5	Fault signal output				
6	Fault detect				
9	Gnd				
14	Drive signal input(-)				
15	Drive signal input(+)				
4, 7, 8, 10, 11	Not connected				

APPLICATION NOTES

- 1. The IGBT gate-emitter drive loop wiring must be shorter than one meter.
- 2. The IGBT gate-emitter drive loop wiring should be twisted.
- 3. If large voltage spike is generated at the collector of the IGBT, increase the IGBT gate resistor.
- 4. Pins which not be used must not be connected with the application circuit.
- 5. The external blocking capacitors must be connected as close as possible to the driver's pin.
- Peak reverse voltage of the diode D1 must be higher than the peak value of the IGBT collector voltage.